

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-11. (Cancelled).

Claim 12 (New): A laser anneal device comprising:

 a laser light source;

 an optical system for forming a line-form sheet beam from laser light emitted from the laser light source; and

 a mechanism for changing a relative position between a semiconductor film and the line-form sheet beam such that the line-form sheet beam scans the semiconductor film in a line width direction while the line-form sheet beam overlaps a previous scan in a predetermined amount; wherein

 the optical system creates a sloped energy level profile in the line-form sheet beam in a line width direction of the line-form sheet beam; and

 the mechanism changes the relative position between a semiconductor film and the line-form sheet beam such that a direction from a position, in the line-form sheet beam in the line width direction, in which the energy level is lower towards a position in which the energy level is higher matches a scan progress direction of the line-form sheet beam with respect to the semiconductor film.

Claim 13 (New): A laser anneal device according to claim 12, wherein

 an energy level at a front position in the scan progress direction of the line-form sheet beam is approximately equal to or greater than a maximum value of an energy level which maximizes a grain size of the semiconductor film.

Claim 14 (New): A laser anneal device according to claim 12, wherein
a peak energy level at a rear position of the line-form sheet beam in
the scan progress direction is less than a maximum value of an energy level which
maximizes a grain size of the semiconductor film.

Claim 15 (New): A laser anneal device according to claim 12, wherein
an energy level at a front position in the scan progress direction of the
line-form sheet beam is approximately equal to or greater than a maximum value of
an energy level which maximizes a grain size of the semiconductor film; and
a peak energy level at a rear position of the line-form sheet beam in
the scan progress direction is less than a maximum value of an energy level which
maximizes a grain size of the semiconductor film.

Claim 16 (New): A laser anneal device according to claim 12, wherein
the semiconductor film to be irradiated with the laser is an amorphous
silicon film; and
an energy level which maximizes a grain size of the semiconductor film
is an energy level which maximizes a grain size of the semiconductor film is an
energy level which maximizes a grain size of a polycrystalline silicon film obtained
by laser annealing the amorphous silicon film.